

64-Bit Read/Write Memories

General Description

The DM5489B/DM7489B, DM54L89A/DM74L89A are fully decoded 64-bit RAMs organized as 16, 4-bit words. The memory is addressed by applying a binary number to the four Address inputs. After addressing, information may be either written into or read from the memory. To write, both the Memory Enable and the Write Enable inputs must be in the logical "0" state. Information applied to the four Write inputs will then be written into the addressed location. To read information from the memory the Memory Enable input must be in the logical "0" state and the Write Enable input in the logical "1" state. Information will be read as the complement of what was written into the memory. When the Memory Enable input is in the logical "1" state, the outputs will go to the logical "1" state.

The "A" suffix on the low power versions is used to denote that full "tenth-power" technology has been employed in building this RAM.

Features

- For application as a "scratch pad" memory with nondestructive read-out
- Fully decoded memory organized as 16 words of four bits each
- Fast access time

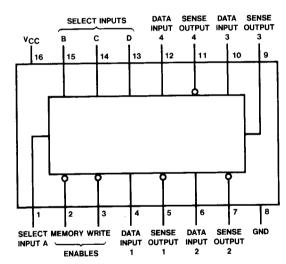
DM54/74—35 ns typical DM54L/74L—110 ns

- Diode-clamped, buffered inputs
- Open-collector outputs provide wire-OR capability
- Typical power dissipation

DM54/74—400 mW DM54L/74L—75 mW

■ Pin compatible with 3101, MM5501

Connection Diagram



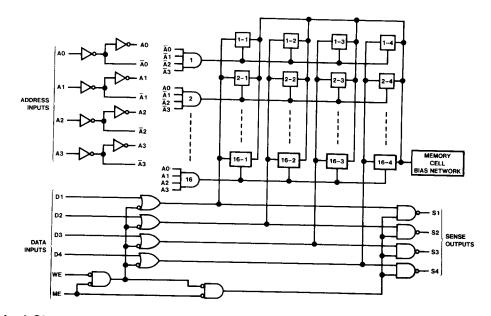
5489 (J) 54L89A (J,W) 7489 (N) 74L89A (N)

Truth Table

Memory Enable	Write Enable	Operation	Outputs
0	0	Write	Logical "1" State ਯ
o	1	Read	Complement of Data
1	×	Hold	Stored in Memory Logical "1" State



Logic Diagram



Electrical Characteristics Over recommended operating free-air temperature range (unless otherwise noted)

_		The state of the state o									
					DM54/74			DM54/74			
	Parameter		Conditions			89		L89A			Units
			Min T				Max	Min	Typ (1)	Max	1
ΛIH	High Level Input Voltage				2			2			V
VIL	Low Level Input Voltage						0.8			0.7	v
VI	Input Clamp Voltage	V _{CC} = Min, I _j = -12 mA					-1.5		 	-1.5	V
ICEX High Level Output Curren	High Level Output Current	V _{CC} = Min, V _I	H = 2 V	DM54			100		 	50	
		V _{IL} = Max, V _{OH} =)H = 5.5 V	DM74			20		 	50	μА
IOL Low Level Output C	Low Level Output Current			DM54			12		<u> </u>	2.0	
				DM74			12			3.6	mA
VOL	VOL Low Level Output Voltage	VCC = Min, VIH = 2 V	H = 2 V	DM54			0.4			0.3	-
		VIL = Max, IOL = Max		V _{IL} = Max, I _{OL} = Max DM74			0.4			0.4	V
-l ₁	Input Current at Maximum Input Voltage	V _{CC} = Max, V _I = 5.5 V					1			0.1	mA
lH.	High Level Input Current	V _{CC} = Max, V _I = 2.4 V					40			10	μΑ
IL Low Level Input Current	V _{CC} = Max V _I = 0.3 V							-0.18	μΑ		
		100 1110	V ₁ =	0.4 V			-1.6				mA
ICC	Supply Current	V _{CC} = Max (2))			80	120		15	19	mA
СО	Off-State Output Capacitance	V _{CC} = 5 V, V _O = 2.0 V, f = 1 MHz			6			N/A	19	pF	

Note 1: All typical values are at V_{CC} = 5 V, T_A = 25°C.

Note 2: I_{CC} is measured with all inputs grounded.



Switching Characteristics V_{CC} = 5 V, T_A = 25°C

			DM54/74				DM54/74L			
	Parameter		89		Conditions	L89A			Units	
, a.a.			Min Typ		Max		Min	Тур	Max	
^t PLH	Propagation Delay Time, Low-to-High Level Output From Memory Enable	C _L = 30 pF R _{L1} = 300 Ω R _{L2} = 600 Ω		23	35	CL = 50 pF RL = 4 kΩ		64	90	ns
^t PHL	Propagation Delay Time, High-to-Low Level Output From Memory Enable			23	35			33	60	ns
^t PLH	Propagation Delay Time, Low-to-High Level Output From Select			34	50			90	150	ns
[†] PHL	Propagation Delay Time. High-to-Low Level Output From Select			35	50			78	150	ns
tSR	Sense Recovery Time After Writing			35	50			110	165	ns
tw	Width of Write-Enable Pulse		40			_	50			ns
tSETUP	Setup Time, Data Input With Respect to Write Enable		0				0			ns
tSETUP	Select Input Setup Time With Respect to Write Enable		0				0			ns
tHOLD	Hold Time, Data Input With Respect to Write Enable		0				0			ns
tHOLD	Select Input Hold Time After Writing		5				0			ns